



**DSS8110Y** 

#### 100V NPN LOW SATURATION TRANSISTOR IN SOT363

#### **Features**

- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 1A high Continuous Collector Current
- I<sub>CM</sub> = 3A Peak Pulse Current
- $R_{CE(sat)} = 200 m\Omega$  for a Low Equivalent On-Resistance
- Low Saturation Voltage V<sub>CE(sat)</sub> < 200mV @ 1A</li>
- Complementary PNP Type Available (DSS9110Y)
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

Case: SOT363

- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (approximate)

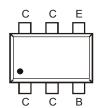
SOT-363







Device Symbol



Pin-Out Top

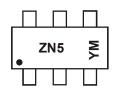
### **Ordering Information** (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS8110Y-7	ZN5	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



ZN5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021
Code	Х	Υ	Z	Α	В	C	D	Е	F	G	Н	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current - Continuous	Ic	1	Α
Peak Pulse Collector Current	I <sub>CM</sub>	3	Α
Base Current – Continuous	I <sub>B</sub>	0.3	Α

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	625	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	200	°C/W
Thermal Resistance, Junction to Lead (Note 6)	$R_{ heta JL}$	81	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

#### ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

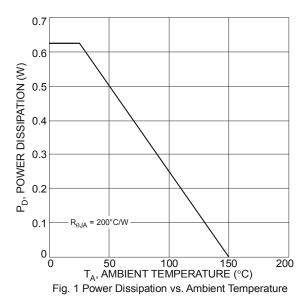
- 5. For a device mounted on minimum recommended pad layout that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

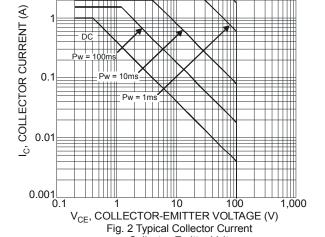
  Thermal resistance from junction to solder-point (at the end of collector lead).

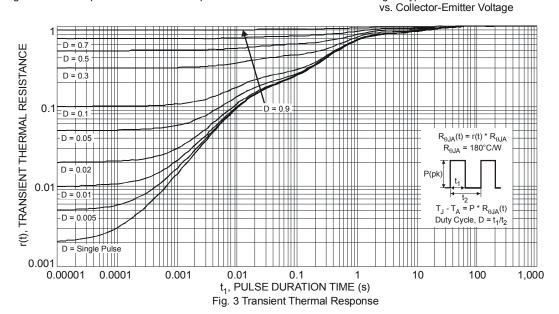
  Refer to JEDEC specification JESD22-A114 and JESD22-A115.



#### **Thermal Characteristics and Derating Information**







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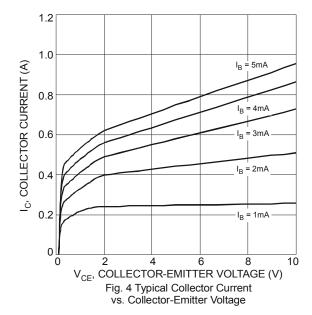


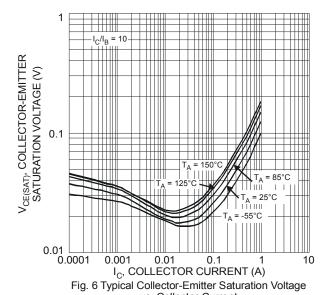
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

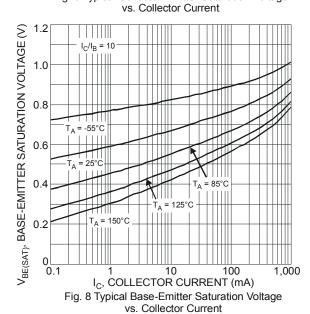
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	120	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	100		_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	_	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_		100	nA 	$V_{CB} = 80V, I_E = 0$
0 11 1 0 1 11 0		_	_	50	μA	$V_{CB} = 80V, I_E = 0, T_A = 150^{\circ}C$
Collector Cutoff Current	I <sub>CES</sub>	_		100	nA	$V_{CE} = 80V, V_{BE} = 0$
Emitter Cutoff Current	I <sub>EBO</sub>	_	—	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 8)						
		150		_		$V_{CE} = 10V$ , $I_C = 1mA$
DC Current Gain	h <sub>FE</sub>	150	_	500	V	$V_{CE} = 10V, I_{C} = 250mA$
	, -	100	_	_		V <sub>CE</sub> = 10V, I <sub>C</sub> = 500mA
		80	_			$V_{CE} = 10V, I_{C} = 1A$
		_	_	40		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	_	_	120	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	_	200		$I_C = 1A$ , $I_B = 100mA$
Collector-Emitter Saturation Resistance	R <sub>CE(sat)</sub>	_	_	200	mΩ	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	_	1.05	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Turn On Voltage	V <sub>BE(on)</sub>	_	_	0.9	V	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1A
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	$C_{obo}$	_	_	7.5	pF	V <sub>CB</sub> = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	_	_	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 50mA, f = 100MHz

Notes: 8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .









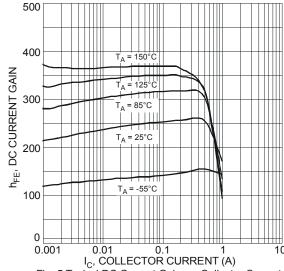
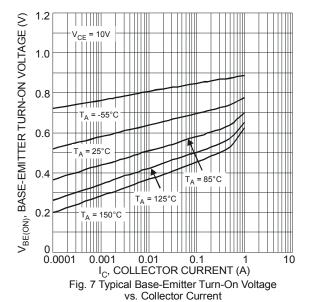


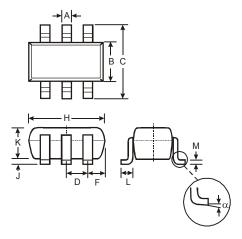
Fig. 5 Typical DC Current Gain vs. Collector Current





## **Package Outline Dimensions**

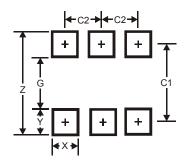
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT363							
Dim	Min	Max	Тур					
Α	0.10	0.30	0.25					
В	1.15	1.35	1.30					
С	2.00	2.20	2.10					
D		0.65 Typ						
F	0.40	0.45	0.425					
Н	1.80	2.20	2.15					
J	0	0.10	0.05					
K	0.90	1.00	1.00					
L	0.25	0.40	0.30					
М	0.10	0.22	0.11					
α	0°	8°	-					
All	All Dimensions in mm							

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Υ	0.6
C1	1.9
C2	0.65

July 2014



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